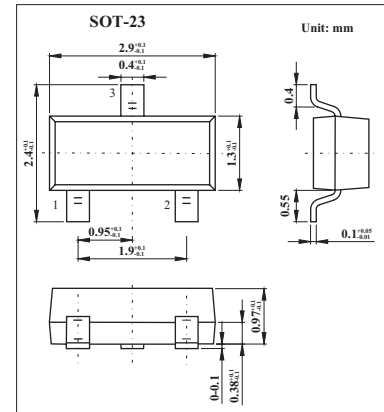
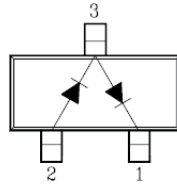


Silicon Epitaxial Planar Diode

KDS226

■ Features

- Low Forward Voltage.: $V_F=0.9V$ (Typ.)
- Fast Reverse Recovery Time: $t_{rr}=1.6ns$ (Typ).
- Small Total capacitance: $C_T=0.9pF$ (Typ.)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Forward Current	I_o	100	mA
Maximum (Peak) Forward Current	I_{FM}	300	mA
Surge Current (10mS)	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=1mA$		0.60		V
		$I_F=10mA$		0.72		
		$I_F=100mA$		0.90	1.20	
Reverse Current	I_R	$V_R=80V$			0.5	μA
Total Capacitance	C_T	$V_R=0V, f=1MHz$		0.9	3.0	pF
Reverse Recovery Time	t_{rr}	$I_F=10mA$		1.6	4.0	nS

■ Marking

Marking	C3
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